Transistors

4V Drive Nch MOSFET **RSQ045N03**

Structure

Silicon N-channel MOSFET

Features

- 1) Low On-resistance.
- 2) Space saving, small surface mount package (TSMT6).
- 3) Low voltage drive (4V drive).

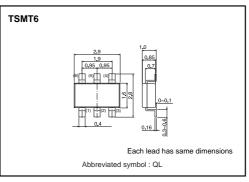
Applications

Switching

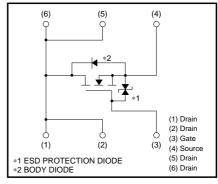
Packaging specifications

	Package	Taping	
Туре	Code	TR	
	Basic ordering unit (pieces)	3000	
RSQ045N03		0	

•Dimensions (Unit : mm)



Inner circuit



Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit	
Drain-source voltage		V _{DSS}	30	V	
Gate-source voltage		V _{GSS}	20	V	
Droin ourrant	Continuous	ID	±4.5	А	
Drain current	Pulsed	I _{DP} *1	±18	А	
Source current	Continuous	ls	1.0	А	
(Body diode)	Pulsed	I _{SP} *1	18	А	
Total power dissipation		P _D *2	1.25	W	
Channel temperature		Tch	150	°C	
Range of storage temperature		Tstg	-55 to +150	°C	

*1 Pw≤10µs, Duty cycle≤1% *2 Mounted on a ceramic board

Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	100	°C/W

* Mounted on a ceramic board



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•Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Gate-source leakage	lgss	-	-	10	μA	Vgs=20V, Vds=0V	
Drain-source breakdown voltage	V(BR) DSS	30	-	-	V	I _D = 1mA, V _{GS} =0V	
Zero gate voltage drain current	IDSS	-	-	1	μA	V _{DS} = 30V, V _{GS} =0V	
Gate threshold voltage	VGS (th)	1.0	-	2.5	V	V _{DS} = 10V, I _D = 1mA	
Static drain-source on-state resistance		-	27	38	mΩ	I _D = 4.5A, V _{GS} = 10V	
	$R_{DS(on)^*}$	-	36	51	mΩ	I _D = 4.5A, V _{GS} = 4.5V	
		-	40	56	mΩ	I _D = 4.5A, V _{GS} = 4V	
Forward transfer admittance	Y _{fs} *	3.5	-	_	S	V _{DS} = 10V, I _D = 4.5A	
Input capacitance	Ciss	-	520	_	pF	V _{DS} = 10V	
Output capacitance	Coss	-	150	-	рF	Vgs=0V	
Reverse transfer capacitance	Crss	-	95	-	рF	f=1MHz	
Turn-on delay time	td (on) *	-	12	-	ns	Vdd≒ 15V	
Rise time	tr *	-	19	-	ns	ID= 2.25A	
Turn-off delay time	td (off) *	-	41	_	ns	Vgs= 10V R∟=6.67Ω	
Fall time	t _f *	-	14	_	ns	$R_{G}=10\Omega$	
Total gate charge	Qg *	-	6.8	9.5	nC	V _{DD} ≒15V V _{GS} =5V	
Gate-source charge	Q _{gs} *	-	1.6	-	nC	ID= 4.5A	
Gate-drain charge	Q _{gd} *	-	2.3	_	nC	R∟=3.33Ω Rg=10Ω	

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd	-	-	1.2	V	I _S = 1.0A, V _{GS} =0V

•Electrical characteristic curves

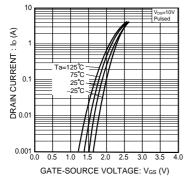


Fig.1 Typical Transfer Characteristics

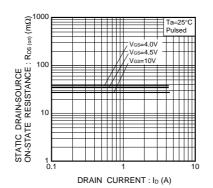


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current (I)

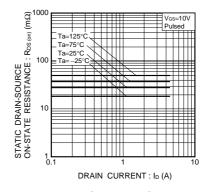
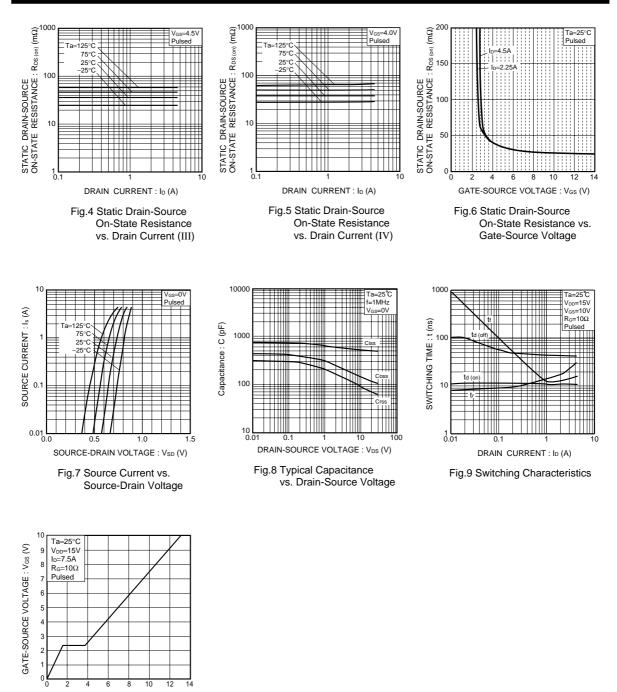


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current (II)

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TOTAL GATE CHARGE : Qg (nC) Fig.10 Dynamic Input Characteristics

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Appendix1-Rev2.0

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